

C850-40P

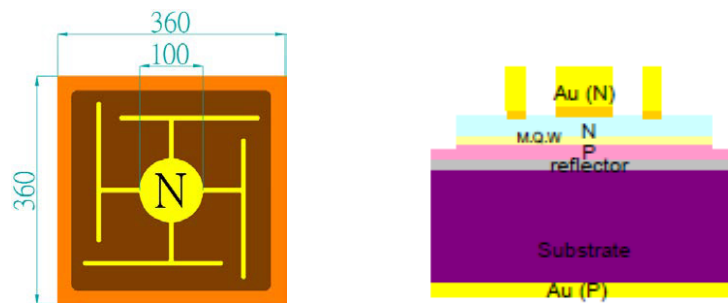
PRELIMINARY

Infrared LED CHIP

<Specifications>

- Materials: AlGaAs
P-pad/Au alloy
N-pad/Au alloy
- Dimensions:
Chip size/360um x 360um
Chip thickness/175um+/-25um
N-pad/100um +/-10um
thickness/3.5 +/-0.3um

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Tc=25°C]			
Item	Symbol	Ratings	Unit
Forward Current	IF	100	mA
Pulse Forward Current*	IFP	1000	mA
Reverse Voltage	VR	10	V
Junction Temperature	Tj	115	°C
Operating Temperature	TOPR	-40 ~ +85	°C
Storage Temperature	TSTG	-20 ~ +65	°C

* Duty 1% and Pulse Width=10us

Electro-Optical Characteristics [Tc=25°C typ.]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF1	IF=50mA	1.3	1.5	2.0	V
	VF2	IF=100mA t=20ms		1.6		
Total Radiated Power	PO1	IF=50mA	15.5	17.0	18.0	mW
	PO2	IF=100mA t=20ms		35.0		
Peak Wavelength	λP	IF=50mA	840		860	nm
Half Width	$\Delta\lambda$	IF=50mA		23		nm

Die shall be mounted on TO-18 gold header without resin coated.(Ta=25°C)